

MOSFETs Silicon N-Channel MOS

# SSM6N57NU

#### 1. Applications

- · Power Management Switches
- · DC-DC Converters

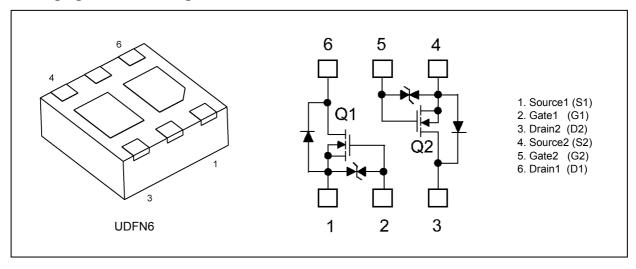
#### 2. Features

- (1) 1.8 V gate drive voltage.
- (2) Low drain-source on-resistance
  - $: R_{DS(ON)} = 39.1 \text{ m}\Omega \text{ (max) } (@V_{GS} = 4.5 \text{ V})$

 $R_{DS(ON)} = 53 \text{ m}\Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$ 

 $R_{\mathrm{DS(ON)}} = 82~\mathrm{m}\Omega~(\mathrm{max})~(@V_{\mathrm{GS}} = 1.8~\mathrm{V})$ 

### 3. Packaging and Pin Configuration





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25°C) (Q1,Q2 Common)

	Characteristics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage			V <sub>GSS</sub>	±12	
Drain current (DC)		(Note 1)	I <sub>D</sub>	4	Α
Drain current (pulsed)		(Note 1), (Note 2)	I <sub>DP</sub>	10	
Power dissipation		(Note 3)	P <sub>D</sub>	1	W
Power dissipation	t ≤ 10 s	(Note 3)	P <sub>D</sub>	2	W
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on a FR4 board.(total dissipation) (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Ta = 25°C unless otherwise specified)(Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	_	_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D$ = 1 mA, $V_{GS}$ = 0 V	30	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	$I_D = 1 \text{ mA}, V_{GS} = -12 \text{ V}$	18	_	_	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS} = 3 \text{ V}, I_{D} = 1 \text{ mA}$	0.4	_	1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D = 2.0 \text{ A}, V_{GS} = 4.5 \text{ V}$	_	30	39.1	mΩ
			$I_D = 1.0 \text{ A}, V_{GS} = 2.5 \text{ V}$	_	37	53	
			I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 1.8 V	_	46	82	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_{D} = 2.0 \text{ A}$	6	12	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current  $(I_D)$  to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

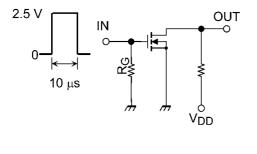
Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)(Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,	_	310	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	20	_	
Output capacitance	Coss			52	_	
Switching time (turn-on time)		$V_{DD}$ = 15 V, $I_{D}$ = 1.0 A $V_{GS}$ = 0 to 2.5 V, $R_{G}$ = 4.7 $\Omega$ ,		26		ns
Switching time (turn-off time)		Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns Ground source, See Chapter 5.3		17	_	

#### 5.3. Switching Time Test Circuit



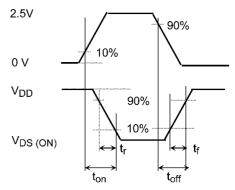


Fig. 5.3.1 Test Circuit of Switching Time

Fig. 5.3.2 Input Waveform/Output Waveform

# 5.4. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		V <sub>DD</sub> = 15 V, V <sub>GS</sub> = 4.5 V,	_	3.2	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$I_D = 4.0 \text{ A}$	_	0.5	_	
Gate-drain charge	Q <sub>gd</sub>		_	0.7	_	

# 5.5. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified) (Q1,Q2 Common)

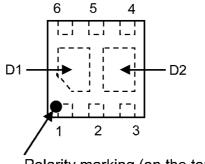
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	$I_D = -4.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	-0.8	-1.2	V

Note 1: Pulse measurement.

#### 6. Marking



Fig. 6.1 Marking



Polarity marking (on the top)
\*Electrodes : on the bottom

Fig. 6.2 Pin Condition(Top View)

## 7. Characteristics Curves (Q1,Q2 Common) (Note)

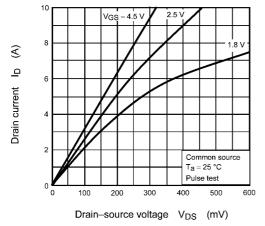
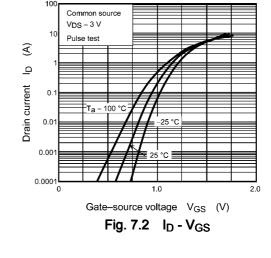


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>



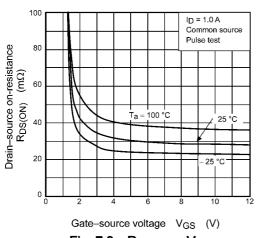


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

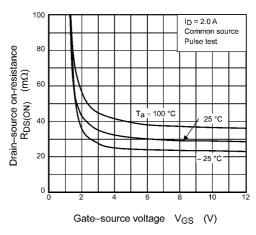


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

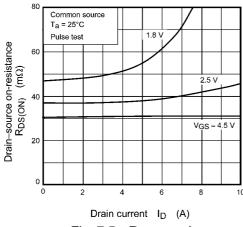


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

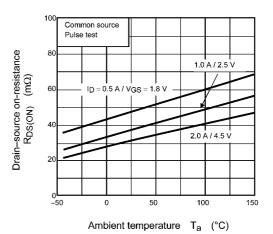
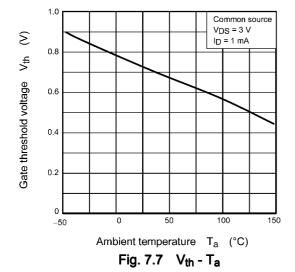


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



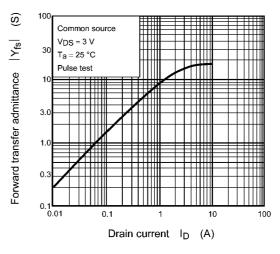
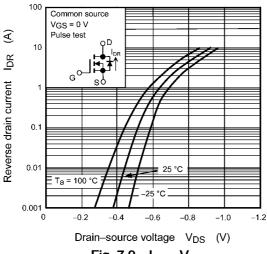


Fig. 7.8 |Yfs| - ID



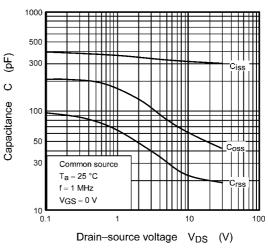
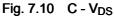
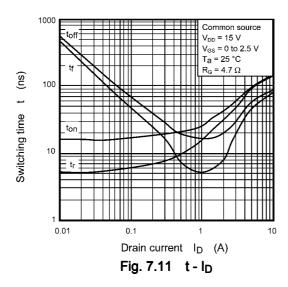


Fig. 7.9  $I_{DR}$  -  $V_{DS}$ 





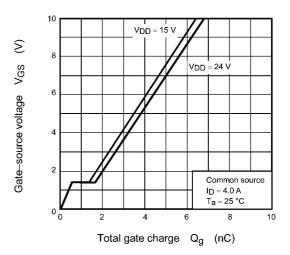
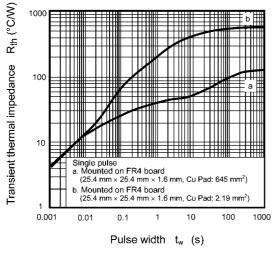


Fig. 7.12 Dynamic Input Characteristics



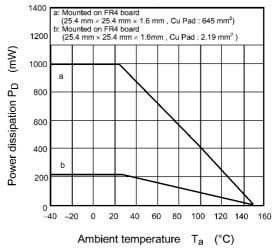


Fig. 7.13 rth - tw

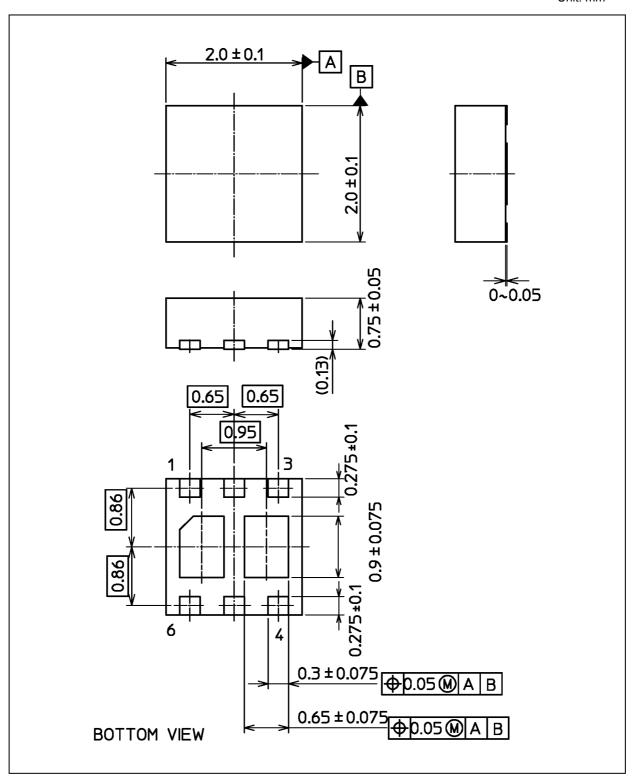
Fig. 7.14 PD - Ta

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 8.5 mg (typ.)

Package Name(s)	
TOSHIBA: 2-2Y1A	
Nickname: UDFN6	



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